

[WeB3] Nitrides for Electronics - III

Session Date	July 15 (Wed.), 2026
Session Time	15:35–17:05
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Okhyun Nam (Tech University of Korea, Korea), Dr. Isabel Streicher (Cornell University, USA)

[WeB3–1]

15:35–15:50

In-Depth Study of Localised Growth of GaN on Silicon Leading to 1 kV, 5 mOhm.cm² Vertical Diodes

M. Charles¹, D. Plaza-Arguello¹, M. El Amrani¹, T. Kaltsounis¹, H. El Rammouz¹, Z. M'Qaddem¹, T. Guillemin², S. Torrenco¹, M. Lafossas¹, N. Rochat¹, Y. Cordier², and J. Buckley¹, ¹CEA Leti, France, ²Univ. Côte d'Azur, France

[WeB3–2]

15:50–16:05

Investigating the Impact of High-Temperature Ohmic Contact Annealing on AlN Schottky Barrier Diodes

Haicheng Cao¹, Mingtao Nong¹, Tingang Liu¹, Zixian Jiang¹, Zhiyuan Liu¹, Saravanan Yuvaraja¹, Xiao Tang², Biplab Sarkar³, Ying Wu¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³Indian Institute of Technology, India

[WeB3–3]

16:05–16:20

Submicron Ultrafast Raman Thermography System for Power Semiconductor Devices and Next Generation Semiconductors.

Jung-Hoon Song^{1,2}, Youngboo Moon^{1,3}, Seungyoung Lim¹, Gye Eun Choi¹, and Jaesun Kim¹, ¹AccuOptotec Co., Korea, ²Kongju National University, Korea, ³UJL Co., Korea

[WeB3–4]

16:20–16:35

Understanding the Impact of n-Type GaN Drift Layer Growth Conditions on 300 mm Wafer Bow for GaN-on-Si Vertical Devices

G. Bouhet, F. Barbier, C. Vergnaud, H. El Rammouz, A. Chaumont, M. Lafossas, P. Valentin, V. Balan, A. Olivier, J. Buckley, C. Masante, M. Charles, and S. Torrenco, CEA-Leti, France

[WeB3-5]

16:35-16:50

SiO_x Interlayer for Reverse Current Suppression in p-GaN Diodes

Zixian Jiang and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[WeB3-6]

16:50-17:05

Crack-Free Si-Doped AlN on Si(111) for Fully Vertical AlN Schottky Barrier Diodes

Haicheng Cao¹, Mingtao Nong¹, Xiao Tang², Biplab Sarkar³, Ying Wu¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³Indian Institute of Technology, India